



SiC-based UV photodiode

Model ST-ABC-L

General Features:

- Broad band UVA+UVB+UVC photodiode
- Photovoltaic mode operation
- TO-46 metal housing
- Good visible blindness
- High responsivity and low dark current

Applications: UV index monitoring, UV radiation dose measurement, flame detection

Specifications:

Parameters	Symbol	Value	Unit
Maximum ratings			
Operation temperature range	T_{opt}	-55-200	°C
Storage temperature range	T_{sto}	-55-200	°C
Soldering temperature (3 s)	T_{sol}	260	°C
Reverse voltage	V_{r-max}	-20	V
General characteristics (25 °C)			
Chip size	A	1	mm ²
Dark current ($V_r = -5$ V)	I_d	<10	pA
Temperature coefficient (@265nm)	T_c	0.065	%/°C
Capacitance (at 0 V and 1 MHz)	C_p	97	pF
Spectral response characteristics (25 °C)			
Wavelength of peak responsivity	λ_p	275	nm

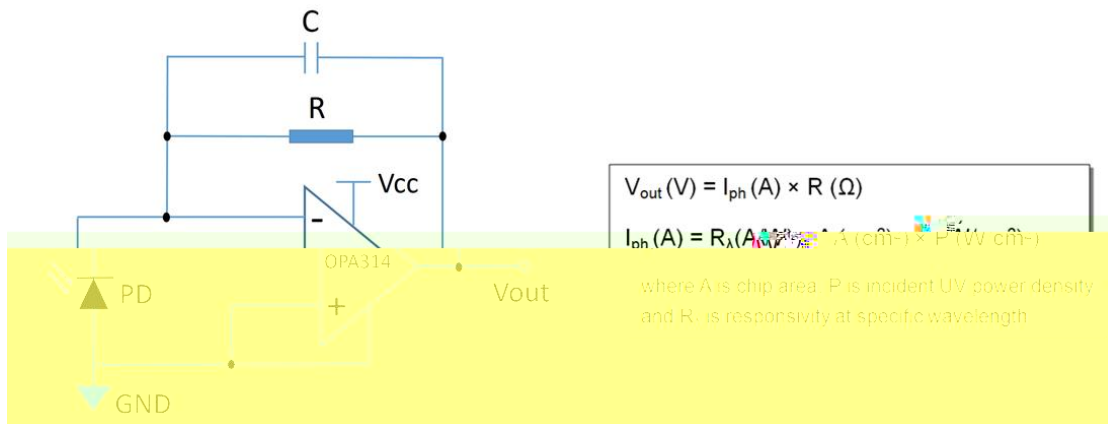
Peak responsivity (at 275



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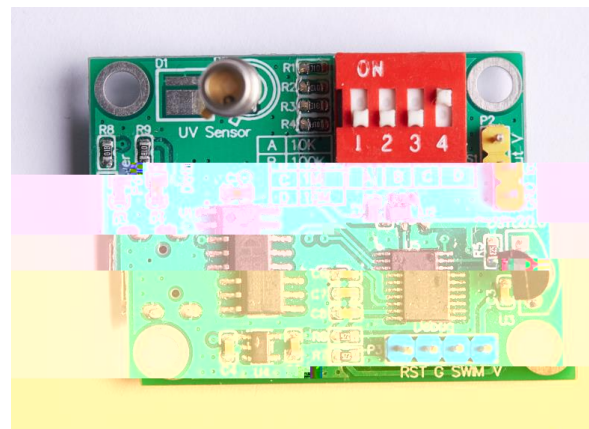
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Application circuit:



Evaluation circuit board:

A small multifunctional amplifier board for developers to simplify and support application development can be separately provided. The evaluation board with one amplifier channel supports both SMD- and TO-type packaged UV photodiodes supplied by GaNo Opto. Users could select one of the two mounting ports for UV photodiode evaluation, while both ports should not be used at the same time.



The evaluation board supports measurement range adjustment function via a dip switch. Different setting of the dip switch corresponds to different load resistance value, which determines the amplification magnitude of the signal processing circuit. A temperature sensor on board is used for embedded temperature compensation.

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